

General Description

It combines planar MOSFET technology with a low resistance package to provide low $R_{DS(ON)}$.

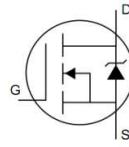
Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Load Switch

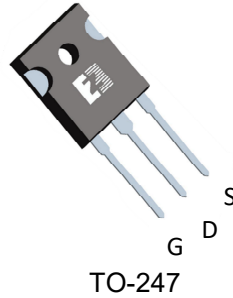
Product Summary



$$V_{DS} = 60V$$

$$R_{DS(ON)} = 4.2m\Omega$$

$$I_D = 160A$$



Ordering Information:

Part NO.	ZMPA070N06HC
Marking	ZMP070N06H
Packing Information	TUBE
Basic ordering unit (pcs)	400

Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		60	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	160	A
	I_D	$T_C=75^\circ C$	115	A
	I_D	$T_C=100^\circ C$	94	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^\circ C$;	640	A
Total Power Dissipation	P_D	$T_C=25^\circ C$	333	W
Total Power Dissipation	P_D	$T_A=25^\circ C$	3.8	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ C$
Storage Temperature	T_{STG}		-55 to +175	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1mH$, $V_{GS}=10V$, $R_g=25\Omega$,	2000	mJ
		$L=0.5mH$, $V_{GS}=10V$, $R_g=25\Omega$,	3600	mJ
ESD Level (HBM)	CLASS 2			

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.45	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{②}$		-	40	°C/W
Soldering temperature (total time<10s)	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.6	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		4.2	6	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		42		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=20A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	5120	-	pF
Output capacitance	C_{oss}		-	1320	-	
Reverse transfer capacitance	C_{rss}		-	450	-	
Gate Resistance	R_g	$f=1MHz$	-	1.2		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	118	-	nC
Gate - Source charge	Q_{gs}		-	12	-	
Gate - Drain charge	Q_{gd}		-	42	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	22	-	ns
Turn-ON Rise time	t_r		-	76	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	98	-	ns
Turn-Off Fall time	t_f		-	30	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=50A$	-	105	-	ns
Reverse Recovery Charge	Q_{RR}		-	210	-	nC

Fig.1 Gate-Charge Characteristics

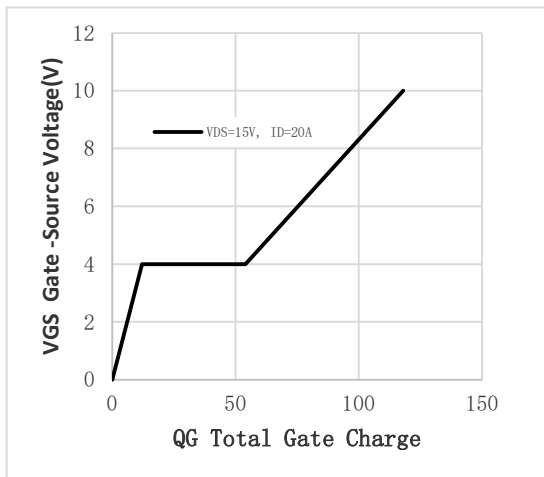


Fig.2 Capacitance Characteristics

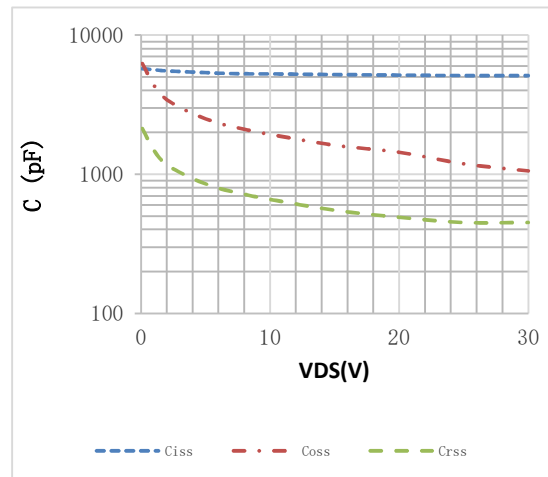


Fig.3 Power Dissipation

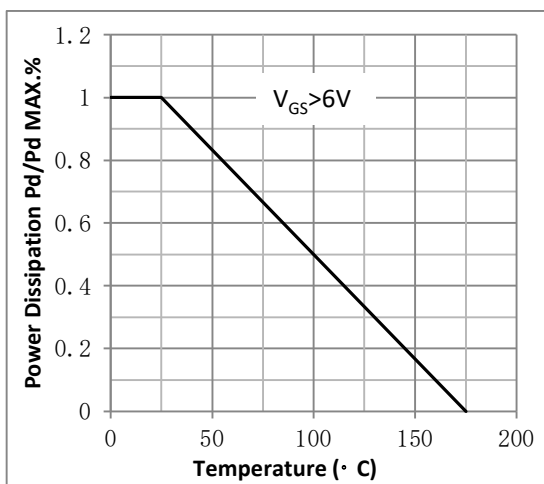


Fig.4 Typical output Characteristics

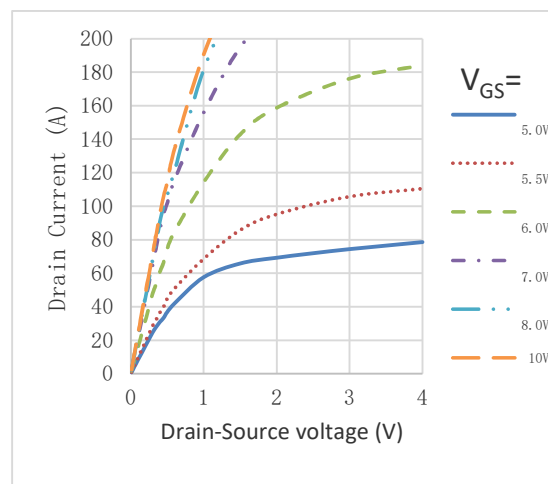


Fig.5 Threshold Voltage V.S Junction Temperature

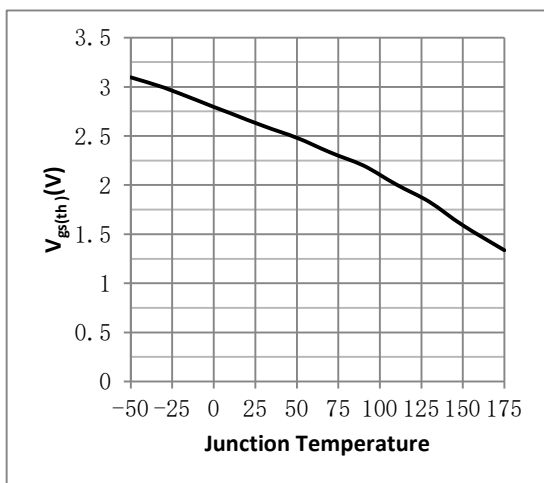


Fig.6 Resistance V.S Drain Current

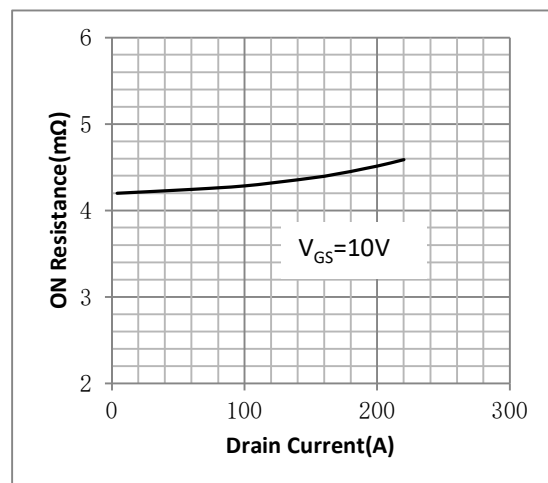


Fig.7 On-Resistance VS Gate Source Voltage

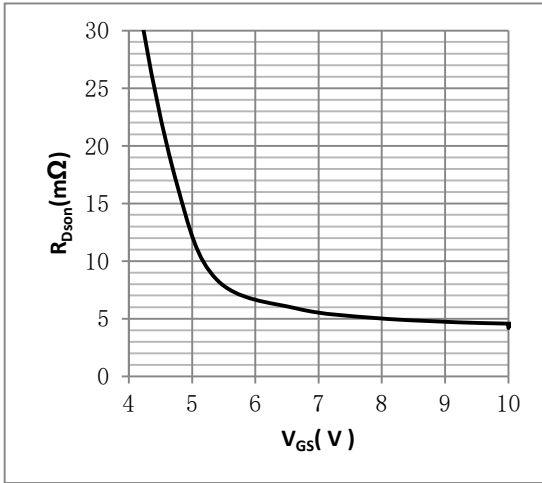


Fig.8 On-Resistance V.S Junction Temperature

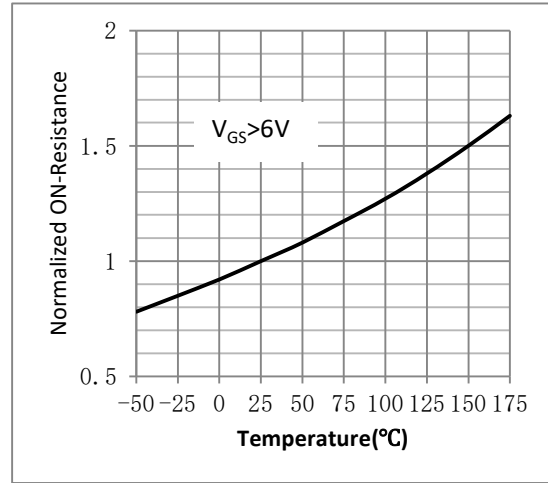


Figure 9. Diode Forward Voltage vs. Current

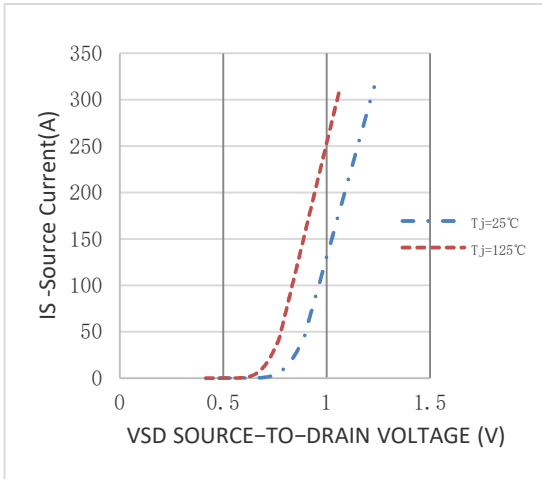


Figure 10. Transfer Characteristics

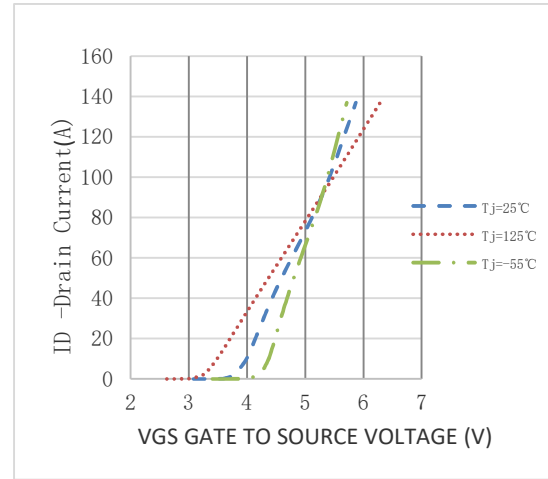


Fig.11 Safe Operating Area

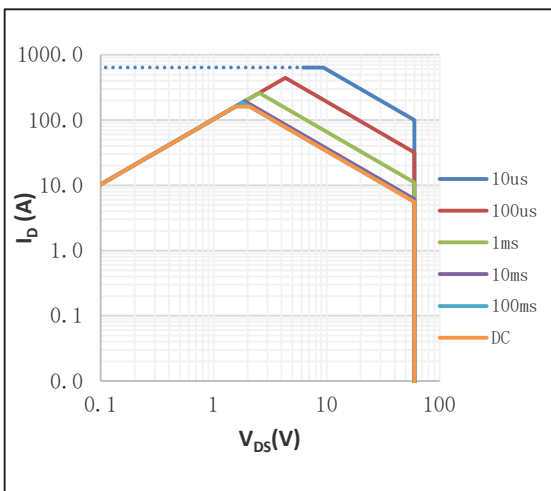
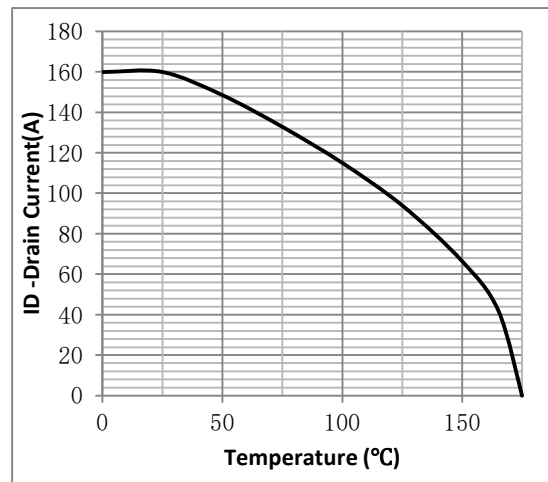
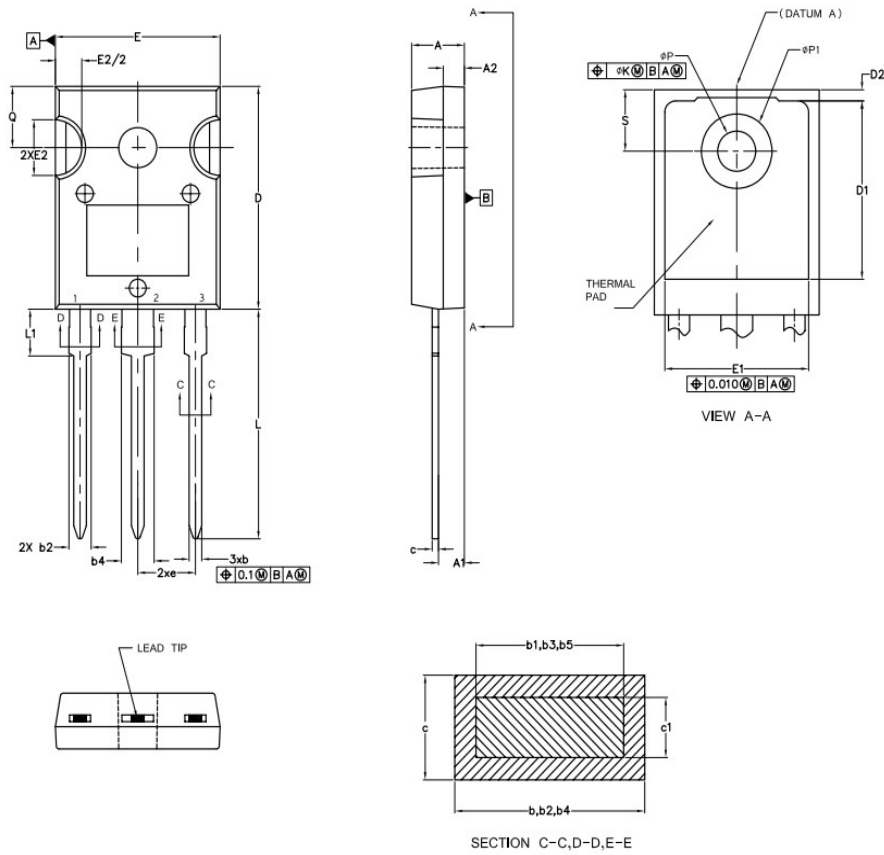


Fig.12 I_D vs. Junction Temperature^③



•TO-247 Package Outline



SYMBOLS	DIMENSIONS			
	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A	4.83	5.13	0.190	0.20
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.65	2.39	0.065	0.094
b3	1.65	2.34	0.065	0.092
b4	2.59	3.43	0.102	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.89	0.015	0.035
c1	0.38	0.84	0.015	0.033
D	19.71	20.70	0.776	0.815
D1	13.08	—	0.515	—
D2	0.51	1.35	0.020	0.053
E	15.29	15.87	0.602	0.625
E1	13.46	—	0.530	—
E2	4.52	5.49	0.178	0.216
e	5.46BSC		0.215BSC	
L	19.57	21.00	0.780	0.827
L1	3.71	4.29	0.146	0.169
φP	3.56	3.66	0.140	0.144
φP1	—	7.39	—	0.291
Q	5.31	5.69	0.209	0.224
S	5.51BSC		0.217BSC	

Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2023.10.6	New
B	2024.7.23	Modified vth typical
C	2024.12.13	Update SOA
D	2025.4.19	Modify POD